

Title (en)

ORGANIC FIELD-EFFECT TRANSISTOR (OFET), A PRODUCTION METHOD THEREFOR, AN INTEGRATED CIRCUIT CONSTRUCTED FROM THE SAME AND THEIR USES

Title (de)

ORGANISCHER FELDEFFEKT-TRANSISTOR (OFET), HERSTELLUNGSVERFAHREN DAZU UND DARAUS GEBaute INTEGRIERTE SCHALTUNG SOWIE VERWENDUNGEN

Title (fr)

TRANSISTOR A EFFET DE CHAMP ORGANIQUE (OFET), PROCEDE DE FABRICATION ET CIRCUIT INTEGRE COMPORTANT CELUI-CI, ET LEURS UTILISATIONS

Publication

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Application

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Abstract (en)

[origin: WO0215293A2] The invention relates to an organic field-effect transistor with an improved performance. The output current is increased by the arrangement of several current channels on the OFET, all of which contribute to the output current. By positioning the source and drain electrode on a plane which is not parallel to the surface of the substrate, it is possible to reduce the distances between the source and the drain in relation to those previously attainable. This produces shorter current channels with faster switching speeds. Finally, the invention relates to integrated circuits, which are stacked on a substrate to save space.

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